

AMENDMENTS TO THE CLAIMS**Claims 1-25. (Withdrawn)**

26. (Currently Amended) A method of forming a diode, comprising the steps of: forming an anode of a first conductivity type and a cathode of a second conductivity type disposed below said anode on a first region of a substrate, wherein at least one of said cathode and anode comprise a plurality of vertically abutting diffusion regions; and forming etching said substrate adjacent said first region to form a plurality of isolation regions, said cathode and anode being disposed between adjacent ones of said plurality of isolation regions, said plurality of isolation regions extending deeper into said substrate [[that]] than said cathode and said anode.
27. (Original) The method as recited in claim 26, wherein said isolation regions comprise a plurality of insulation-filled trenches having sidewalls that are substantially vertical.
28. (Original) The method as recited in claim 26, wherein said isolation regions comprise a plurality of insulation-filled trenches having sidewalls that are tapered.
29. (Original) The method as recited in claim 26, wherein said step of forming said cathode comprises:
forming a first doped region of a second conductivity type abutting said anode; and
forming a second doped region of said second conductivity type abutting and disposed below said first doped region and contacting said substrate, said first and second doped regions having different dopant concentrations.

BUR9-2002-0014-US1

Page 4 of 12

30. (Currently Amended) The method as recited in claim 29, further comprising the step of: forming a second pair of isolation structures disposed between said adjacent adjacent isolation regions and said anode.
31. (Original) The method as recited in claim 26, wherein said isolation regions are formed by a process comprising the steps of:
etching said substrate to form trenches;
depositing at least one insulator; and
removing portions of said insulator outside of said trenches.
32. (Currently Amended) The method as recited in claim 31, wherein said step of depositing comprises a first formation of a liner and a deposition of a fill material.
33. (Currently Amended) The method as recited in claim 26 claim 29, wherein said step of forming said cathode further comprises the step of
forming a third doped region disposed between said first doped region and said second doped region.
34. (Original) The method as recited in claim 33, wherein said third doped region comprises a retrograde-doped region.
35. (Original) The method as recited in claim 26, wherein said step of forming said anode comprises the steps of:
forming a first doped region abutting said cathode; and
forming a second doped region on a surface of said substrate, said second doped region having a higher concentration of dopant than said first doped region.

BUR9-2002-0014-US1

36. (Original) The method as recited in claim 35, wherein said first doped region comprises a retrograde-doped region.
37. (Original) The method as recited in claim 35, further comprising the steps of: forming a plurality of diffusion regions of said second conductivity type on a surface of said substrate.
38. (Currently Amended) The method as recited in claim 37, further comprising the step of: forming a plurality of second ~~isolation~~ isolation regions that separate said plurality of diffusion regions from said cathode.

BUR9-2002-0014-US1

Page 6 of 12